APPENDIX

Amended Claims Shown Without Revision Marks

B1

1 (Once Amended). A method of processing a semiconductor substrate, comprising the steps of:

(a) providing a semiconductor substrate having a surface with a contact formed therein;

(b) depositing a conductor layer on the semiconductor substrate surface, wherein said conductor layer comprises a conductor;

(c) forming an impurity layer in said conductor layer after a portion of the conductive material has been deposited, said impurity layer having a melting point temperature and surface tension less than that of said conductor; and

(d) heating the conductor layer to a reflow temperature, said reflow temperature being sufficient to cause the layers to reflow.

B2

30 (Once Amended). A method of forming a contact, the method comprising the following steps performed in order:

(a) providing a substrate having a contact hole formed therein, the contact hole exposing a portion of a conductive area of the substrate;

(b) depositing conductive material into the contact hole, the conductive material having a melting point;

(c) depositing an impurity into the contact hole after a portion of the conductive material has been deposited, the impurity causing the melting point of the conductive material to lower; and

B2

(d) reflowing the conductive material and the impurity.

B3

40 (Once Amended). A method of forming a contact, the method comprising the steps of:

(a) providing a substrate having a contact hole formed therein, the contact hole exposing a portion of a conductive area of the substrate;

(b) depositing conductive material into the contact hole, the conductive material having a surface tension; and

(c) depositing an impurity onto the conductive material, after a portion of the conductive material has been deposited, at a temperature that causes the conductive material to reflow, the impurity causing the surface tension of the conductive material to lower.

B4

48 (Once Amended). A method of filling a feature having a high aspect ratio, the method comprising the steps of:

(a) depositing conductive material into the high aspect ratio feature, the conductive material having a surface tension; and

(b) depositing an impurity onto the conductive material, after 70% of the conductive material has been deposited, at a temperature that causes the conductive material to reflow, the impurity causing the surface tension of the conductive material to lower.

60 (Once Amended). A method of forming a contact, the method comprising the steps of:

(a) providing a substrate having a contact hole formed therein, the contact hole exposing a portion of a conductive area of the substrate;

(b) depositing conductive material into the contact hole, the conductive material having a surface tension; and

(c) after a portion of the conductive material has been deposited, depositing an impurity which does not migrate out of the contact hole onto the conductive material at a temperature that causes the conductive material to reflow, the impurity causing the surface tension of the conductive material to lower.